查询KTD1028供应商 捷多邦，专业PCB打样工厂，24小时加急出货

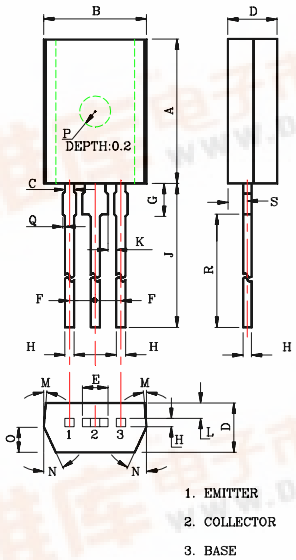
KEL
KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR
TECHNICAL DATA

KTD1028
EPITAXIAL PLANAR NPN TRANSISTOR

HIGH CURRENT APPLICATION.

FEATURES
- High DC Current Gain
  : h_{FE}=800～3200 (V_{CE}=5.0V, I_C=300mA).
- Wide Area of Safe Operation.
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$=0.17V (I_C=500mA, I_B=5.0mA).



DIM	MILLIMETERS
A	7.20 MAX
B	5.20 MAX
C	0.60 MAX
D	2.50 MAX
E	1.15 MAX
F	1.27
G	1.70 MAX
H	0.55 MAX
J	14.00±0.50
K	0.35 MIN
L	0.75±0.10
M	4°
N	25°
O	1.25
P	ø1.50
Q	0.10 MAX
R	12.50±0.50
S	1.00

TO-92L

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	8	V
Collector Current	I_C	1.0	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=60V, I_E=0	-	-	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=8V, I_C=0	-	-	100	nA
DC Current Gain	h_{FE}(1) Note	V_{CE}=5.0V, I_C=300mA	800	1500	3200	
	h_{FE}(2)	V_{CE}=5.0V, I_C=1.0A	400	-	-	
Collector-Emitter Saturration Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=5.0mA	-	0.17	0.30	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA, I_B=5.0mA	-	0.80	1.2	V
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz	-	18	30	pF
Transition Frequency	f_T	V_{CE}=10V, I_C=500mA	150	250	-	MHz
Base-Emitter Voltage	V_{BE}	V_{CE}=5V, I_C=100mA	600	630	700	mV

Note: h_{FE} Classification A:800～1600, B:1200～2400, C:2000～3200

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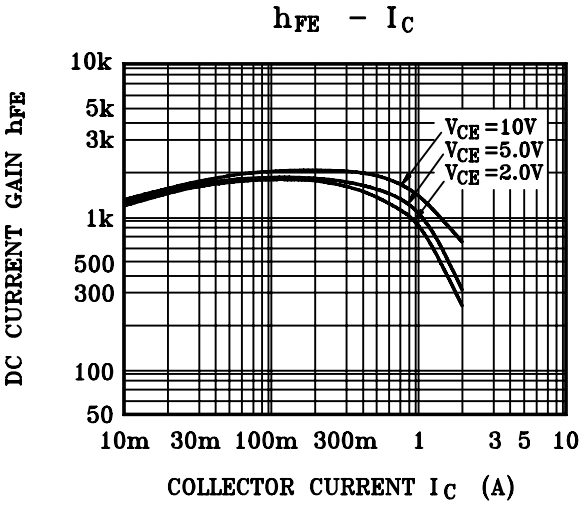
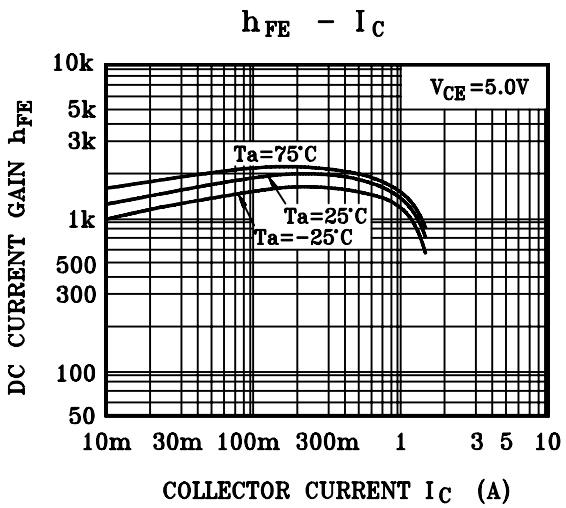
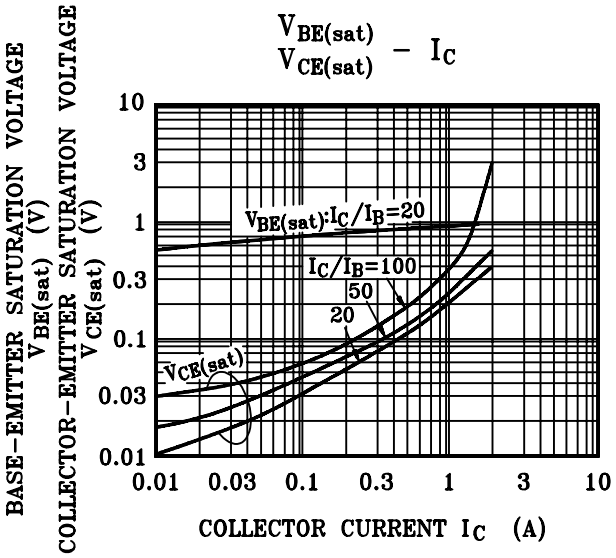
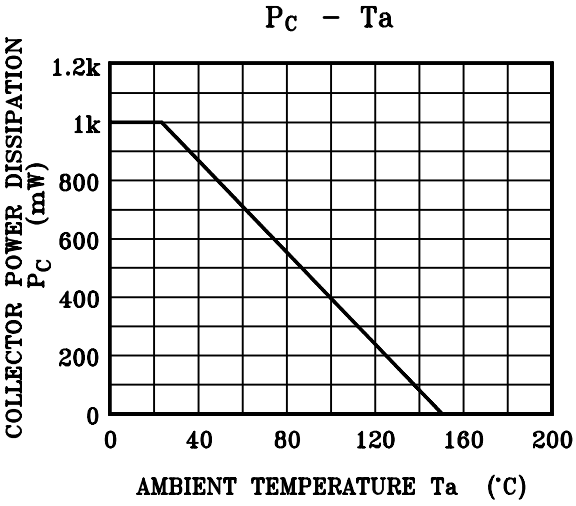
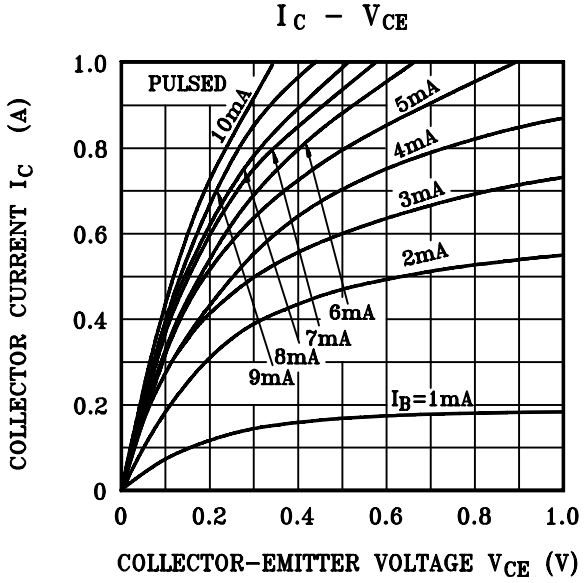

hFE – IC
DC CURRENT GAIN hFE
10k
5k
3k
1k
500
300
100
50
VCE =10V
VCE =5.0V
VCE =2.0V
10m 30m 100m 300m 1 3 5 10
COLLECTOR CURRENT IC (A)


hFE – IC
DC CURRENT GAIN hFE
10k
5k
3k
1k
500
300
100
50
VCE =5.0V
Ta=75°C
Ta=25°C
Ta=−25°C
10m 30m 100m 300m 1 3 5 10
COLLECTOR CURRENT IC (A)


VBE(sat)
VCE(sat) – IC
BASE−EMITTER SATURATION VOLTAGE VBE(sat) (V)
COLLECTOR−EMITTER SATURATION VOLTAGE VCE(sat) (V)
10
3
1
0.3
0.1
0.03
0.01
VBE(sat):IC/IB=20
IC/IB=100
50
20
VCE(sat)
0.01 0.03 0.1 0.3 1 3 10
COLLECTOR CURRENT IC (A)


PC – Ta
COLLECTOR POWER DISSIPATION PC (mW)
1.2k
1k
800
600
400
200
0
0 40 80 120 160 200
AMBIENT TEMPERATURE Ta (°C)


IC – VCE
COLLECTOR CURRENT IC (A)
1.0
0.8
0.6
0.4
0.2
0
PULSED
10mA
5mA
4mA
3mA
2mA
6mA
7mA
8mA
9mA
IB=1mA
0 0.2 0.4 0.6 0.8 1.0
COLLECTOR−EMITTER VOLTAGE VCE (V)